

2N5400

PNP EPITAXIAL SILICON TRANSISTOR

T-29-21

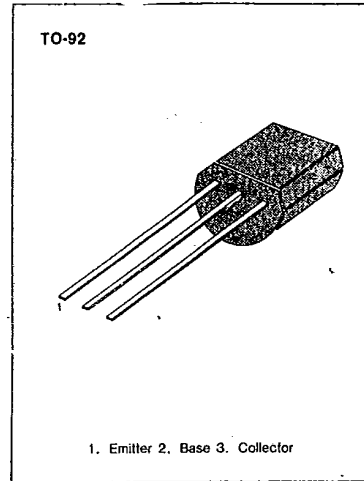
AMPLIFIER TRANSISTOR

- Collector-Base Voltage: $V_{CBO} = 120V$
- Collector Dissipation: $P_C (\text{max}) = 625mW$

ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ C$)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	130	V
Collector-Emitter Voltage	V_{CEO}	120	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	600	mA
Collector Dissipation	P_C	625	mW
Junction Temperature	T_J	150	$^\circ C$
Storage Temperature	T_{stg}	-55 ~ 150	$^\circ C$

* Refer to 2N5401 for graphs

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ C$)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV_{CBO}	$I_C = 100\mu A, I_E = 0$	130			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C = 1mA, I_B = 0$	120			V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E = 10\mu A, I_C = 0$	5			V
Collector Cut-off Current	I_{CBO}	$V_{CB} = 100V, I_E = 0$			100	nA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = 3V, I_C = 0$			50	nA
DC Current Gain	h_{FE}	$I_C = 1mA, V_{CE} = 5V$	30			
		$I_C = 10mA, V_{CE} = 5V$	40		180	
		$I_C = 50mA, V_{CE} = 5V$	40			
Collector-Emitter Saturation Voltage	$V_{CE} (\text{sat})$	$I_C = 10mA, I_B = 1mA$			0.2	V
		$I_C = 50mA, I_B = 5mA$			0.5	V
Base-Emitter Saturation Voltage	$V_{BE} (\text{sat})$	$I_C = 10mA, I_B = 1mA$			1	V
		$I_C = 50mA, I_B = 5mA$			1	V
Current Gain Bandwidth Product	f_T	$I_C = 10mA, V_{CE} = 10V$ $f = 100MHz$	100		400	MHz
Output Capacitance	C_{ob}	$V_{CB} = 10V, I_E = 0$ $f = 1MHz$			6	pF
Noise Figure	NF	$I_C = 250\mu A, V_{CE} = 5V$ $R_S = 1K\Omega$ $f = 10Hz \text{ to } 15.7KHz$			8	dB

* Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$